

Complementary power Darlington transistors

Features

- Good h_{FE} linearity
- High f_T frequency
- Monolithic Darlington configuration with integrated antiparallel collector-emitter diode

Applications

- Linear and switching industrial equipment

Description

The devices are manufactured in planar technology with "base island" layout and monolithic Darlington configuration.

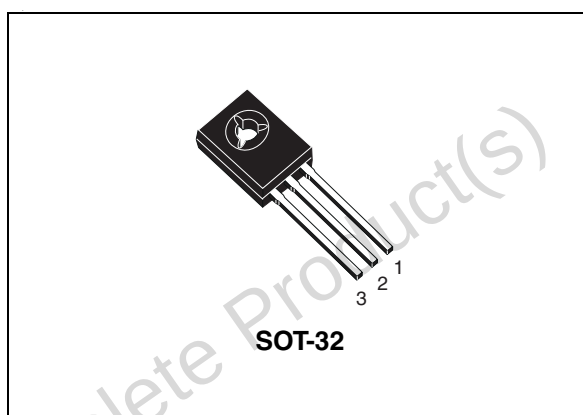


Figure 1. Internal schematic diagram

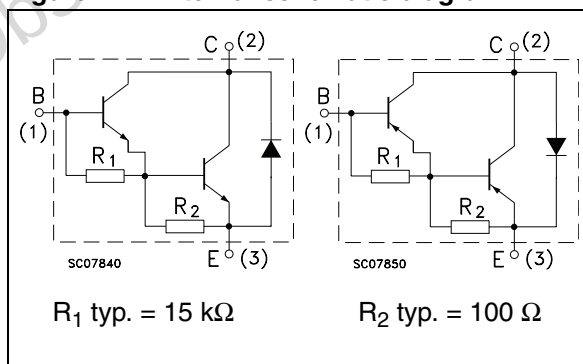


Table 1. Device summary

Order codes	Marking	Polarity	Package	Packaging
2N6036	2N6036	NPN	SOT-32	Tube
2N6039	2N6039	PNP	SOT-32	Tube

1 Absolute maximum ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base voltage ($I_E = 0$)	80	V
V_{CEO}	Collector-emitter voltage ($I_B = 0$)		
V_{EBO}	Emitter-base voltage ($I_C = 0$)	5	V
I_C	Collector current	4	A
I_{CM}	Collector peak current	8	A
I_B	Base current	0.1	A
P_{TOT}	Total dissipation at $T_{case} = 25^\circ\text{C}$	40	W
T_{STG}	Storage temperature	-65 to 150	$^\circ\text{C}$
T_J	Max. operating junction temperature	150	$^\circ\text{C}$

Note: For PNP types voltage and current values are negative.

2 Electrical characteristics

($T_{\text{case}} = 25\text{ }^{\circ}\text{C}$; unless otherwise specified)

Table 3. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{CEV}	Collector cut-off current ($V_{\text{BE}} = -1.5\text{ V}$)	$V_{\text{CE}} = 80\text{ V}$ $V_{\text{CE}} = 80\text{ V}, T_{\text{c}} = 125\text{ }^{\circ}\text{C}$		-	0.1 0.5	mA mA
I_{CBO}	Collector cut-off current ($I_{\text{E}} = 0$)	$V_{\text{CB}} = 80\text{ V}$		-	0.1	mA
I_{CEO}	Collector cut-off current ($I_{\text{B}} = 0$)	$V_{\text{CE}} = 80\text{ V}$		-	0.1	mA
I_{EBO}	Emitter cut-off current ($I_{\text{C}} = 0$)	$V_{\text{EB}} = 5\text{ V}$		-	2	mA
$V_{\text{CEO(sus)}}^{(1)}$	Collector-emitter sustaining voltage	$I_{\text{C}} = 100\text{ mA}$	80	-		V
$V_{\text{CE(sat)}}^{(1)}$	Collector-emitter saturation voltage	$I_{\text{C}} = 2\text{ A}$ $I_{\text{B}} = 8\text{ mA}$		-	2	V
		$I_{\text{C}} = 4\text{ A}$ $I_{\text{B}} = 40\text{ mA}$		-	3	
$V_{\text{BE(sat)}}^{(1)}$	Base-emitter saturation voltage	$I_{\text{C}} = 4\text{ A}$ $I_{\text{B}} = 40\text{ mA}$		-	4	V
$V_{\text{BE(on)}}$	Base-emitter on voltage	$I_{\text{C}} = 2\text{ A}$ $V_{\text{CE}} = 3\text{ V}$		-	2.8	V
$h_{\text{FE}}^{(1)}$	DC current gain	$I_{\text{C}} = 0.5\text{ A}$ $V_{\text{CE}} = 3\text{ V}$	500	-		
		$I_{\text{C}} = 2\text{ A}$ $V_{\text{CE}} = 3\text{ V}$	750	-	15000	
		$I_{\text{C}} = 4\text{ A}$ $V_{\text{CE}} = 3\text{ V}$	100	-		
h_{fe}	Small signal current gain	$I_{\text{C}} = 0.75\text{ A}$ $V_{\text{CE}} = 10\text{ V}$ $f = 1\text{ MHz}$	25	-		
C_{CBO}	Collector base capacitance ($I_{\text{E}} = 0$)	$V_{\text{CB}} = 10\text{ V}$ $f = 0.1\text{ MHz}$ for 2N6036 for 2N6039		-	100 200	pF pF

1. Pulsed duration = 300 μs , duty cycle 1.5%.

Note: For PNP types voltage and current values are negative.

2.1 Typical characteristic (curves)

Figure 2. DC current gain
($V_{CE} = 3\text{ V NPN}$)

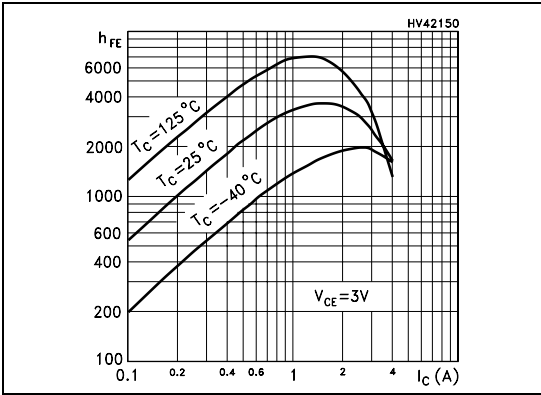


Figure 3. DC current gain
($V_{CE} = -3\text{ V PNP}$)

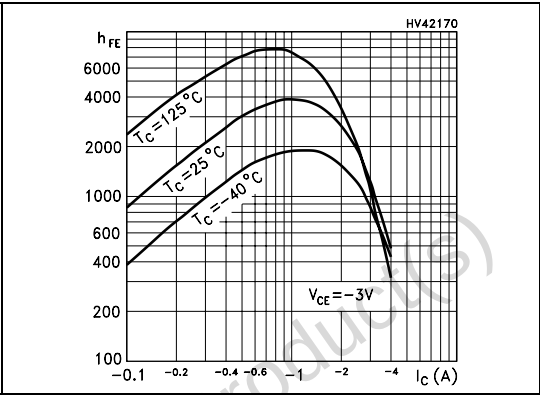


Figure 4. DC current gain
($V_{CE} = 5\text{ V NPN}$)

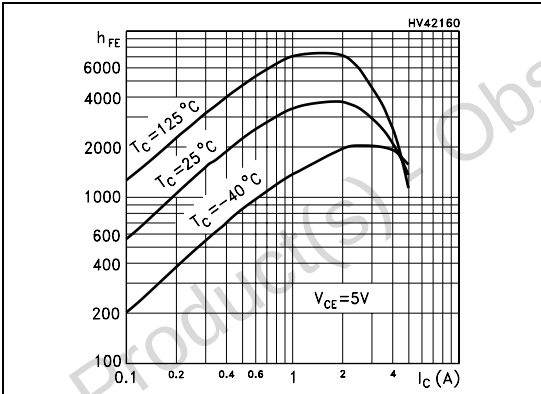


Figure 5. DC current gain
($V_{CE} = -5\text{ V PNP}$)

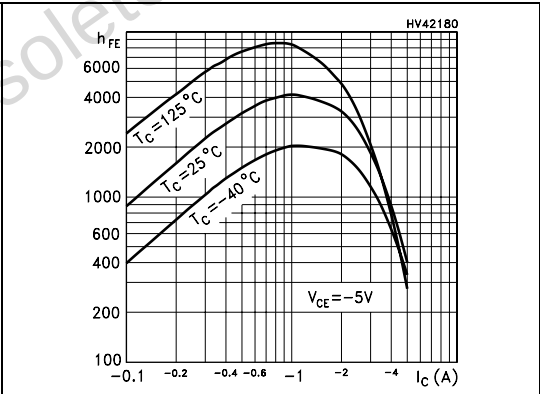


Figure 6. Collector-emitter saturation voltage (NPN)

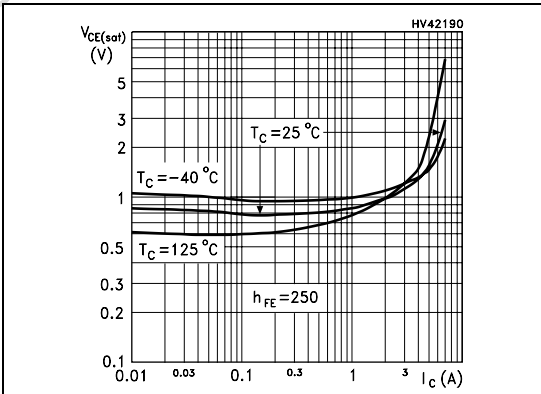


Figure 7. Collector-emitter saturation voltage (PNP)

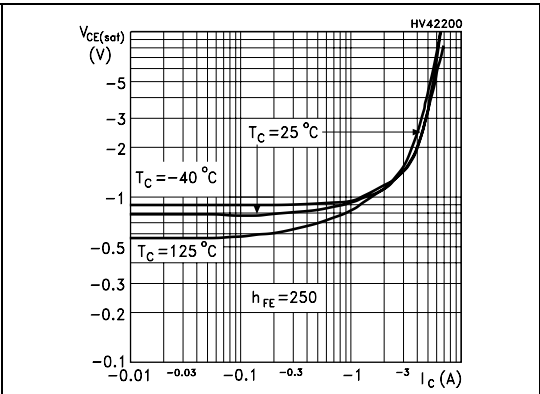


Figure 8. Base-emitter saturation voltage (NPN)

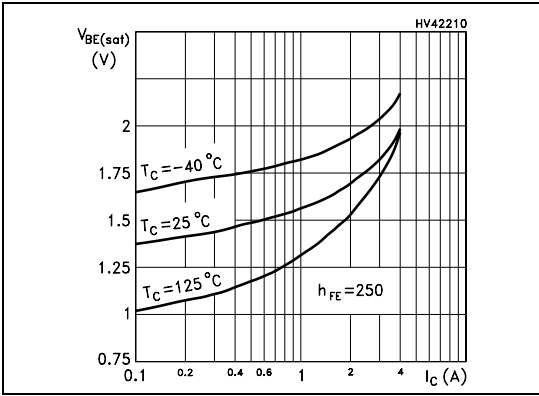


Figure 9. Base-emitter saturation voltage (PNP)

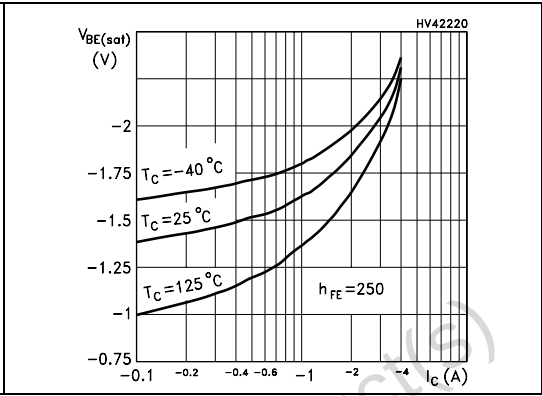


Figure 10. Base-emitter on voltage (NPN)

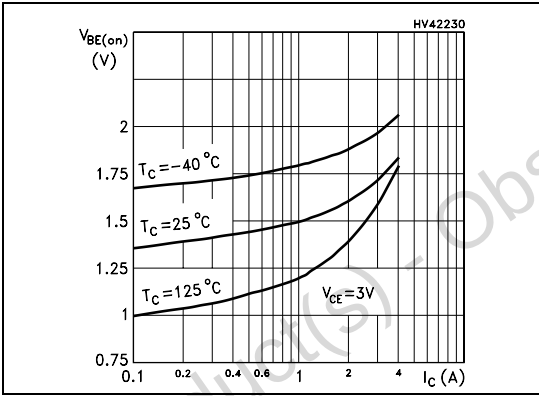


Figure 11. Base-emitter on voltage (PNP)

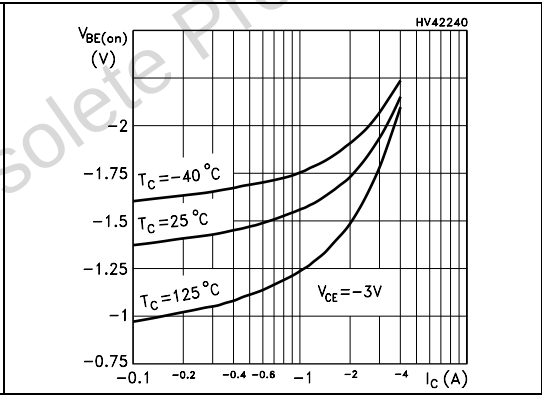


Figure 12. Resistive load switching time (NPN, on)

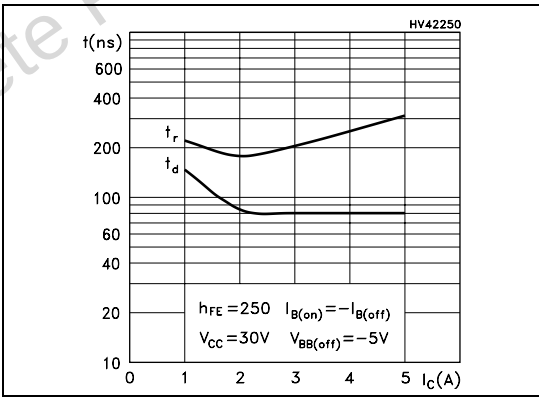


Figure 13. Resistive load switching time (PNP, on)

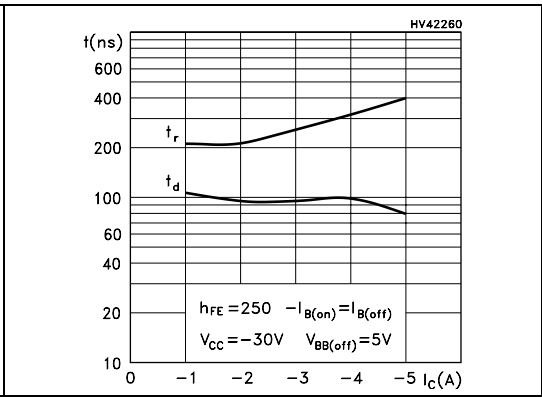
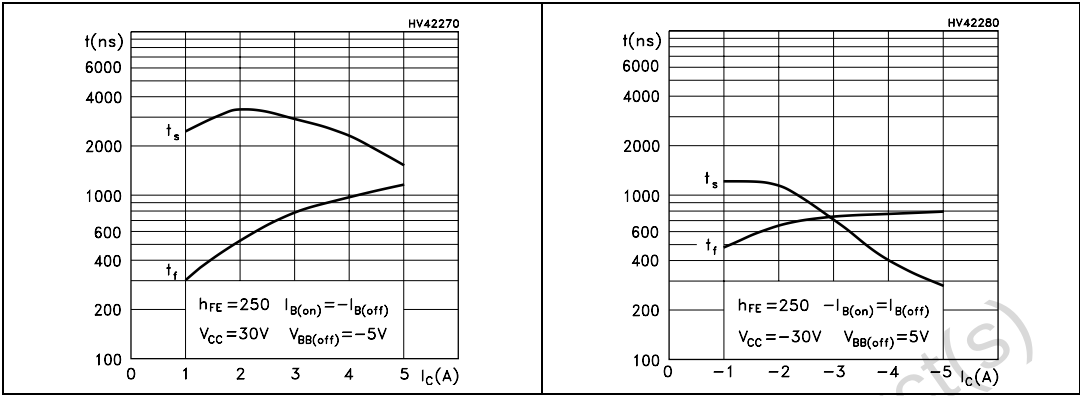


Figure 14. Resistive load switching time (NPN, off) Figure 15. Resistive load switching time (PNP, off)



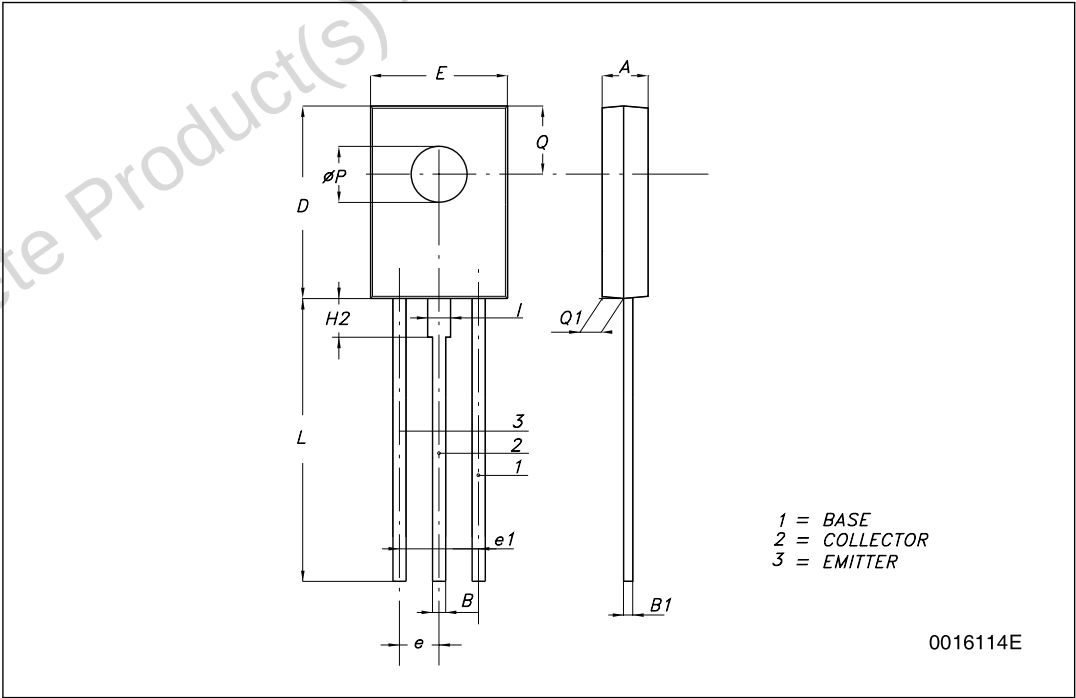
3 Package mechanical data

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Obsolete Product(s) - Obsolete Product(s)

SOT-32 (TO-126) MECHANICAL DATA

DIM.	mm.		
	MIN.	TYP	MAX.
A	2.4		2.9
B	0.64		0.88
B1	0.39		0.63
D	10.5		11.05
E	7.4		7.8
e	2.04	2.29	2.54
e1	4.07	4.58	5.08
L	15.3		16
P	2.9		3.2
Q		3.8	
Q1	1		1.52
H2		2.15	
I		1.27	



4 Revision history

Table 4. Document revision history

Date	Revision	Changes
21-Jun-2004	4	Document migration, no content change.
20-May-2009	5	Modified SOT-32 mechanical data.

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